AUTOMOTIVE GRADE



AUIRF7478Q

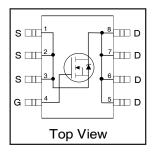
Features

- Advanced Planar Technology
- Low On-Resistance
- Dynamic dV/dT Rating
- 150°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified *

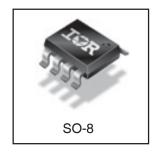
Description

Specifically designed for Automotive applications, this Cellular design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low onresistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.

HEXFET® Power MOSFET



V _{(BR)DSS}	60V		
R _{DS(on)} typ.		20m Ω	
	max.	26m Ω	
I _D		7.0A	



G	D	S
Gate	Drain	Source

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is $25^{\circ}C$, unless otherwise specified.

	Parameter	Max.	Units
V_{DS}	Drain-Source Voltage	60	V
I _D @ T _A = 25°C	Continuous Drain Current, V _{GS} @ 10V	7.0	
I _D @ T _A = 70°C Continuous Drain Current, V _{GS} @ 10V		5.6	Α
I _{DM}	Pulsed Drain Current ①	56	
P _D @T _A = 25°C	Power Dissipation⊕	2.5	W
	Linear Derating Factor	0.02	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
Single Pulse Avalanche Energy ②		140	mJ
I _{AR} Avalanche Current ①		4.2	Α
dv/dt	Peak Diode Recovery dv/dt ®	3.7	V/ns
T_J	Operating Junction and	-55 to + 150	
T _{STG}	Storage Temperature Range	-55 10 + 150	°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Thermal Resistance

	Parameter	Max.	Units
$R_{\theta JL}$	Junction-to-Drain Lead	20	°C/W
$R_{\theta JA}$	Junction-to-Ambient ⁽⁴⁾	50	C/VV

HEXFET® is a registered trademark of International Rectifier.

^{*}Qualification standards can be found at http://www.irf.com/

Static Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Тур.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	60			V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_{J}$	Breakdown Voltage Temp. Coefficient		0.065		V/°C	Reference to 25°C, I _D = 1mA
D	Static Drain-to-Source On-Resistance		20	26	mΩ	$V_{GS} = 10V, I_D = 4.2A$ ③
R _{DS(on)}	Static Dialii-to-Source Off-Resistance		23	30	11152	$V_{GS} = 4.5V, I_D = 3.5A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	1.0		3.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
gfs	Forward Transconductance	17			S	$V_{DS} = 50V, I_{D} = 4.2A$
I _{DSS}	Drain-to-Source Leakage Current			20		$V_{DS} = 48V, V_{GS} = 0V$
				100	μΑ	$V_{DS} = 48V, V_{GS} = 0V, T_{J} = 125^{\circ}C$
I _{GSS}	Gate-to-Source Forward Leakage Gate-to-Source Reverse Leakage			100	nA	V _{GS} = 20V
				-100] ''A	$V_{GS} = -20V$

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Тур.	Max.	Units	Conditions
Q_g	Total Gate Charge		21	31		$I_D = 4.2A$
Q_{gs}	Gate-to-Source Charge		4.3		nC	$V_{DS} = 48V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	_	9.6			$V_{GS} = 4.5V$
t _{d(on)}	Turn-On Delay Time		7.7			$V_{DD} = 30V$
t _r	Rise Time		2.6			$I_D = 4.2A$
$t_{d(off)}$	Turn-Off Delay Time		44		ns	$R_G = 6.2\Omega$
t _f	Fall Time		13			V _{GS} = 10V ③
C _{iss}	Input Capacitance		1740			$V_{GS} = 0V$
C _{oss}	Output Capacitance		300			$V_{DS} = 25V$
C _{rss}	Reverse Transfer Capacitance		37			f = 1.0MHz
C _{oss}	Output Capacitance		1590		pF	$V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0MHz$
C _{oss}	Output Capacitance	_	220			$V_{GS} = 0V, V_{DS} = 48V, f = 1.0MHz$
C _{oss}	Output Capacitance		410			$V_{GS} = 0V, V_{DS} = 0V \text{ to } 48V$ ⑤

Diode Characteristics

	Parameter	Min.	Тур.	Max.	Units	Conditions
Is	Continuous Source Current			0.0		MOSFET symbol
	(Body Diode)			2.3		showing the
I _{SM}	Pulsed Source Current			56	A	integral reverse
	(Body Diode) ①			36		p-n junction diode.
V_{SD}	Diode Forward Voltage			1.3	V	$T_J = 25^{\circ}C$, $I_S = 4.2A$, $V_{GS} = 0V$ ③
t _{rr}	Reverse Recovery Time		52	78	ns	$T_J = 25^{\circ}C, I_F = 4.2A$
Q _{rr}	Reverse Recovery Charge		100	150	nC	di/dt = 100A/µs ③

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- $\label{eq:tarting} \begin{array}{ll} \text{ Starting T}_J = 25^{\circ}\text{C}, \ L = 16\text{mH} \\ \text{R}_G = 25\Omega, \ I_{AS} = 4.2\text{A}. \end{array}$
- When mounted on 1 inch square copper board
- $\ ^{\circ}$ C $_{oss}$ eff. is a fixed capacitance that gives the same charging time as C $_{oss}$ while V $_{DS}$ is rising from 0 to 80% V $_{DSS}$

Qualification Information[†]

		Automotive				
			(per AEC-Q101) ^{††}			
Qualification L		Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.				
Moisture Sensitivity Level		SO-8 MSL1				
	Machine Model		Class M3(+/- 300V) ^{†††}			
		(per AEC-Q101-002)				
	Human Body Model	Class H1C(+/- 2000V) ^{†††}				
ESD	ESD		(per AEC-Q101-001)			
Charged Device Model		Class C5(+/- 2000V) ^{†††}				
			(per AEC-Q101-005)			
RoHS Complia	nt	Yes				

[†] Qualification standards can be found at International Rectifier's web site: http://www.irf.com/

^{††} Exceptions (if any) to AEC-Q101 requirements are noted in the qualification report.

^{†††} Highest passing voltage

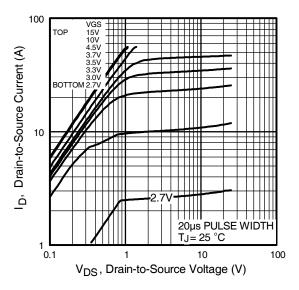


Fig 1. Typical Output Characteristics

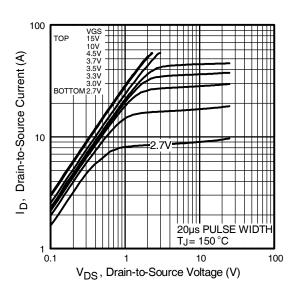


Fig 2. Typical Output Characteristics

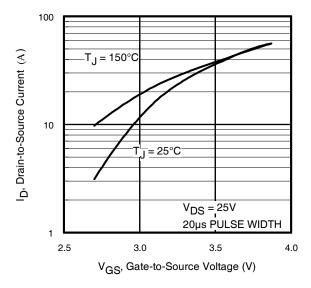


Fig 3. Typical Transfer Characteristics

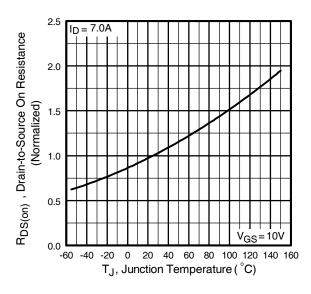


Fig 4. Normalized On-Resistance Vs. Temperature

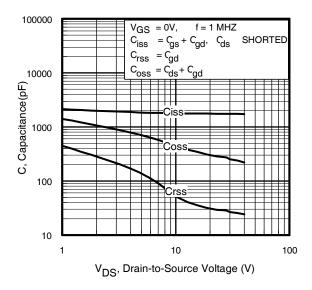


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

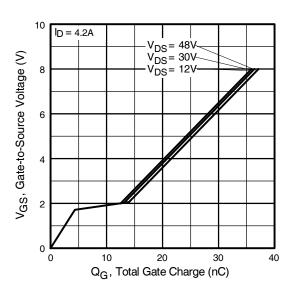


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

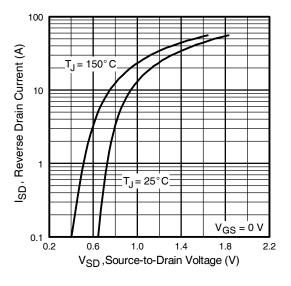


Fig 7. Typical Source-Drain Diode Forward Voltage

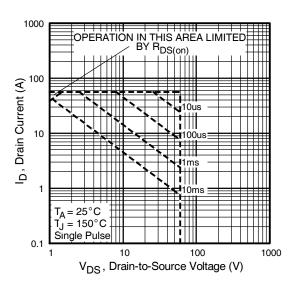


Fig 8. Maximum Safe Operating Area

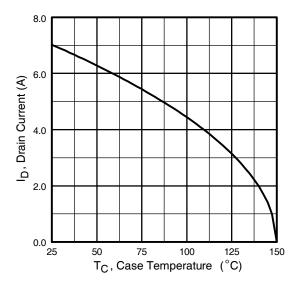


Fig 9. Maximum Drain Current Vs. Ambient Temperature

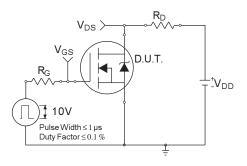


Fig 10a. Switching Time Test Circuit

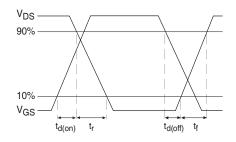


Fig 10b. Switching Time Waveforms

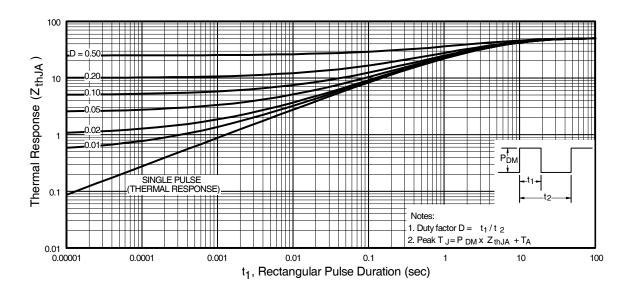


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

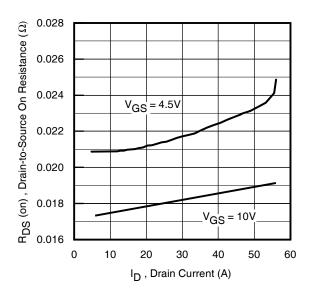


Fig 12. On-Resistance Vs. Drain Current

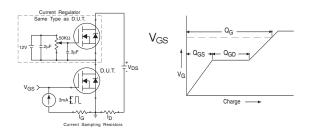


Fig 14a&b. Basic Gate Charge Test Circuit and Waveform

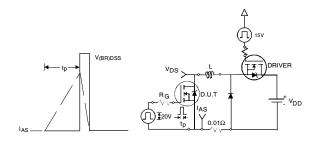


Fig 15a&b. Unclamped Inductive Test circuit and Waveforms

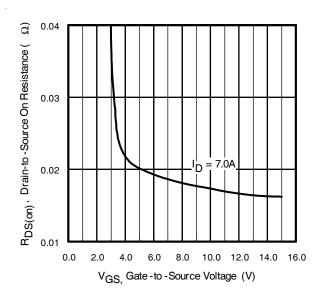


Fig 13. On-Resistance Vs. Gate Voltage

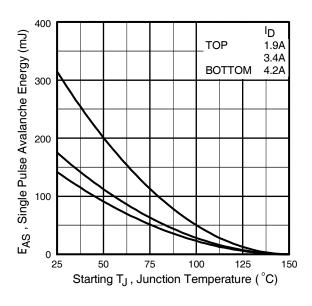
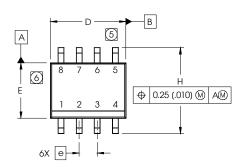


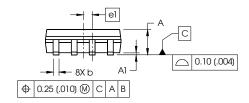
Fig 15c. Maximum Avalanche Energy Vs. Drain Current

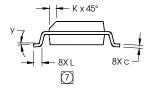
SO-8 Package Outline

Dimensions are shown in millimeters (inches)



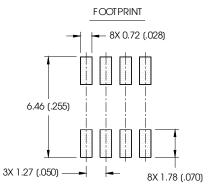
	DIM	INC	HES	MILLIM	ETERS		
	DIIVI	MIN	MAX	MIN	MAX		
ſ	Α	.0532	.0688	1.35	1.75		
ſ	Αl	.0040	.0098	0.10	0.25		
	О	.013	.020	0.33	0.51		
ſ	O	.0075	.0098	0.19	0.25		
	D	.189	.1968	4.80	5.00		
	Е	.1497	.1574	3.80	4.00		
	Φ	.050 B	.050 BASIC		1.27 BASIC		
	еl	.025 B	ASIC	0.635 BASIC			
	Η	.2284	.2440	5.80	6.20		
	Κ	.0099	.0196	0.25	0.50		
ĺ	L	.016	.050	0.40	1.27		
[У	0°	8°	0°	8°		



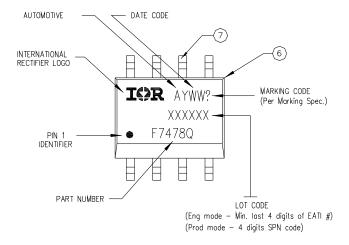


NOTES:

- 1. DIMENSIONING & TOLERANGING PER ASME Y14.5M-1994
- 2. CONTROLLING DIMENSION: MILLIMETER
- 3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
- 4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA
- (5) DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).
- (6) DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).
- (7) DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO ASUBSTRATE.



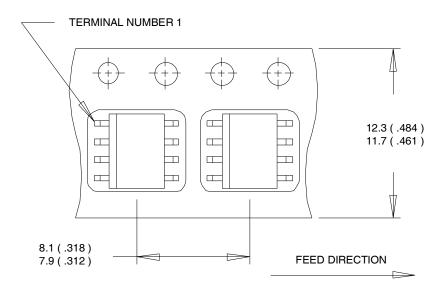
SO-8 Part Marking



TOP MARKING (LASER)

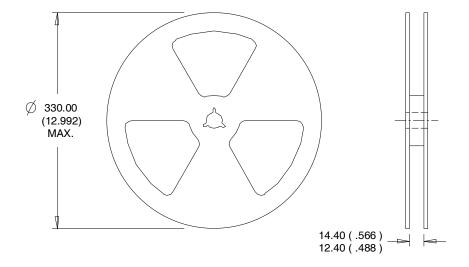
SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)



NOTES:

- 1. CONTROLLING DIMENSION: MILLIMETER.
- 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
- 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES:

- 1. CONTROLLING DIMENSION : MILLIMETER. 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Ordering Information

Base part	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRF7478Q	SO-8	Tube	95	AUIRF7478Q
		Tape and Reel	4000	AUIRF7478QTR

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